

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
100V	23mΩ @ V <sub>GS</sub> = 10V	45A
	30mΩ @ V <sub>GS</sub> = 6V	38A

## Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub> yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

## Applications

- Synchronous rectifiers
- DC-DC converters
- Primary side switching

## Features

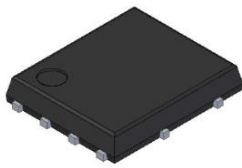
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable And Robust End Application
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**  
<https://www.diodes.com/quality/product-definitions/>
- **An automotive-compliant part is available under separate datasheet ([DMTH10H025LPSQ](#))**

## Mechanical Data

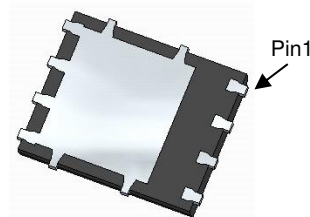
- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

Site 1:

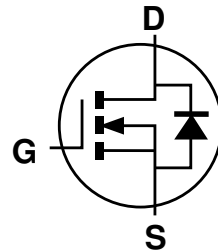
PowerDI5060-8



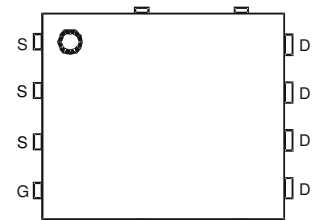
Top View



Bottom View



Internal Schematic



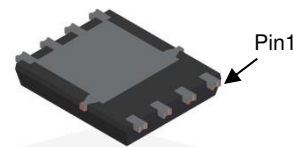
Top View  
Pin Configuration

Site 2:

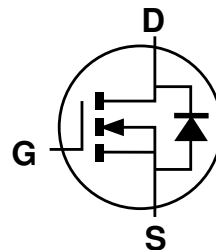
PowerDI5060-8 (SWP) (Type UX)



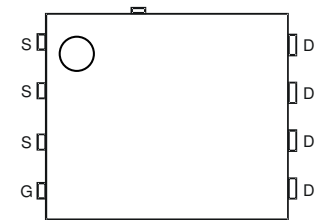
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

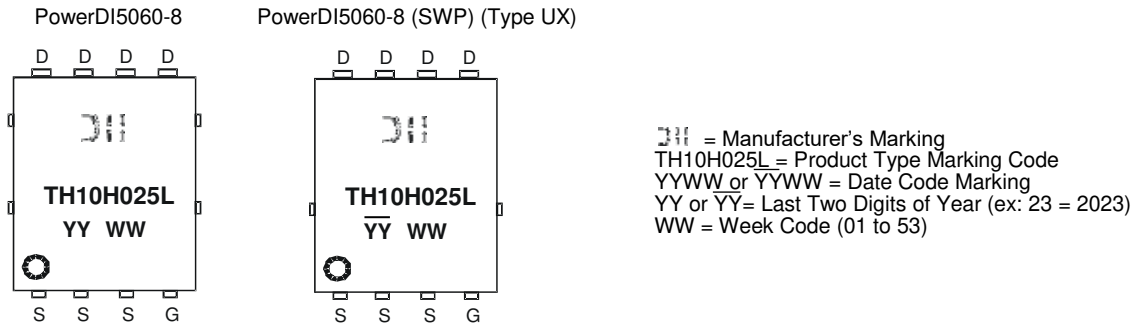
- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H025LPS-13	PowerDI5060-8	2500	Tape & Reel
DMTH10H025LPS-13	PowerDI5060-8 (SWP) (Type UX)	2500	Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	I <sub>D</sub>	T <sub>A</sub> = +25°C	9.3	A
		T <sub>A</sub> = +100°C	6.6	A
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	I <sub>D</sub>	T <sub>C</sub> = +25°C	45	A
		T <sub>C</sub> = +100°C	32	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	90	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	45	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	90	A	
Avalanche Current (Note 7), L=0.1mH	I <sub>AS</sub>	15.8	A	
Avalanche Energy (Note 7), L=0.1mH	E <sub>AS</sub>	12.5	mJ	
Avalanche Current (Note 7), L=3mH	I <sub>AS</sub>	8	A	
Avalanche Energy (Note 7), L=3mH	E <sub>AS</sub>	96	mJ	

## Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θJA</sub>	46	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>C</sub> = +25°C	79	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	1.9	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.  
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 7. Short duration pulse test used to minimize self-heating effect.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	18	23	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	21	30		V <sub>GS</sub> = 6V, I <sub>D</sub> = 12.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	1477	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	263	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	20	—		
Gate Resistance	R <sub>g</sub>	—	1.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	21	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	5.7	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	3.8	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	6.3	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>g</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	—	9.4	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	16.7	—		
Turn-Off Fall Time	t <sub>f</sub>	—	8.2	—		
Reverse Recovery Time	t <sub>RR</sub>	—	38.7	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	53.7	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

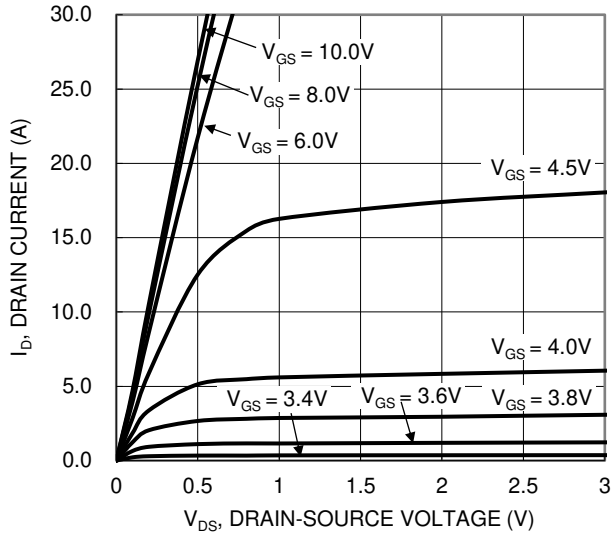


Figure 1. Typical Output Characteristic

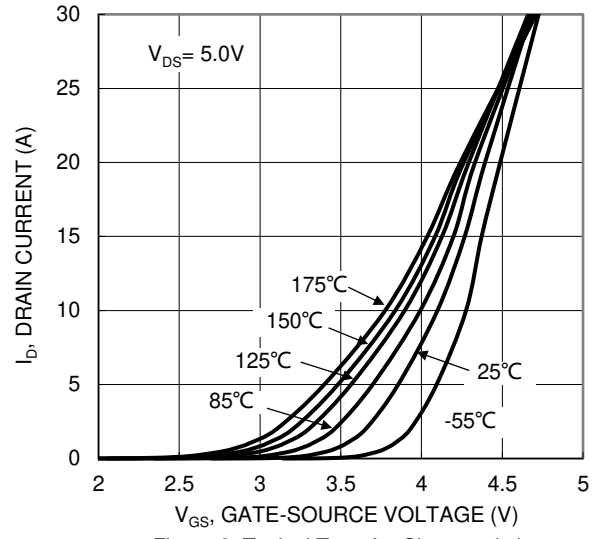


Figure 2. Typical Transfer Characteristic

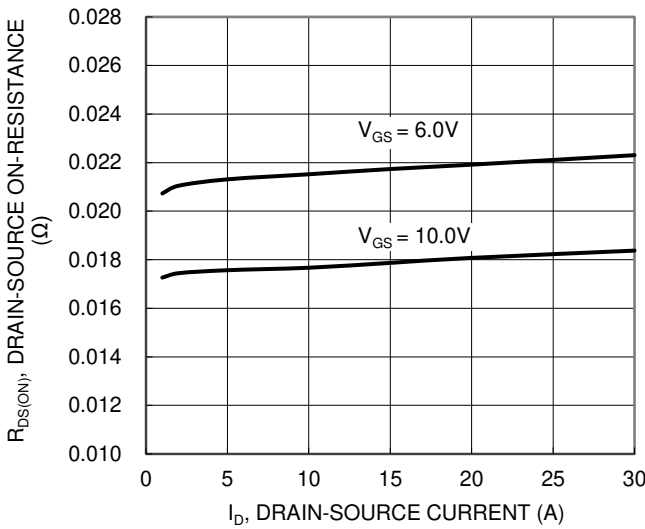


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

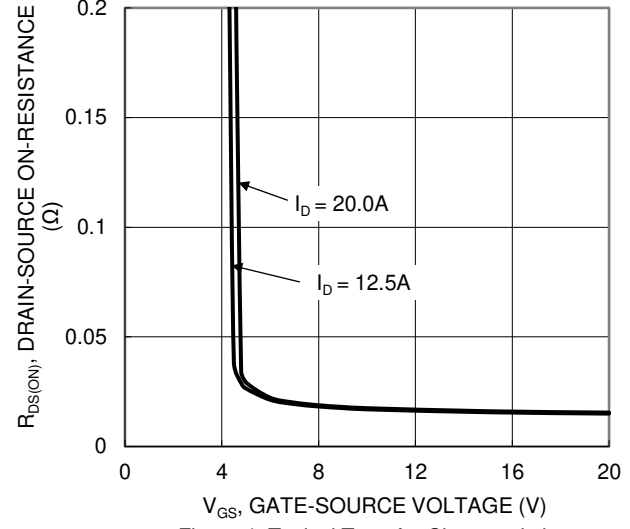


Figure 4. Typical Transfer Characteristic

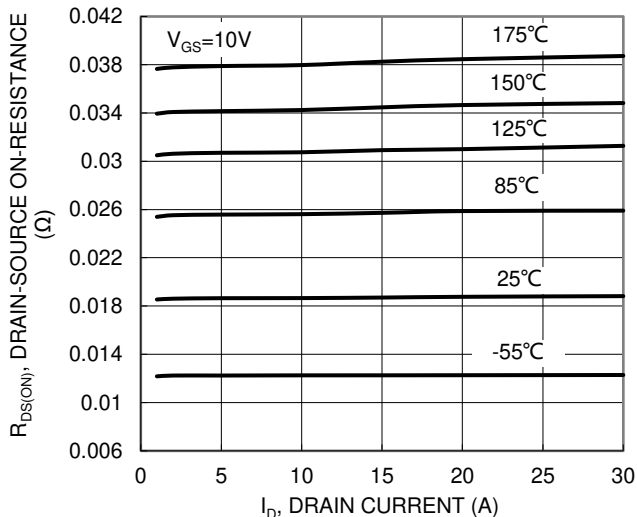


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

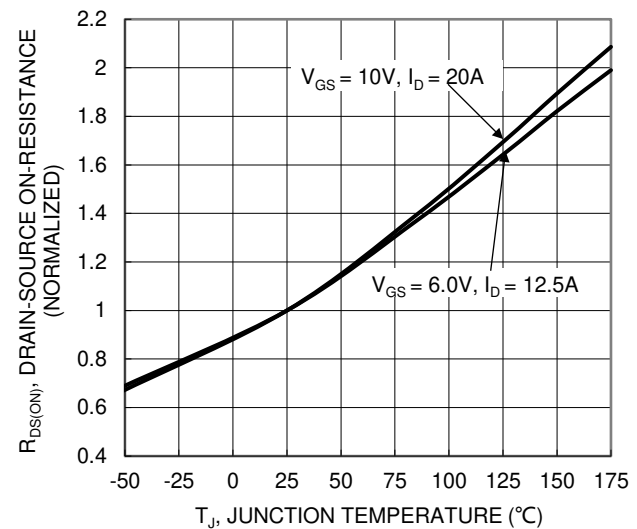


Figure 6. On-Resistance Variation with Temperature

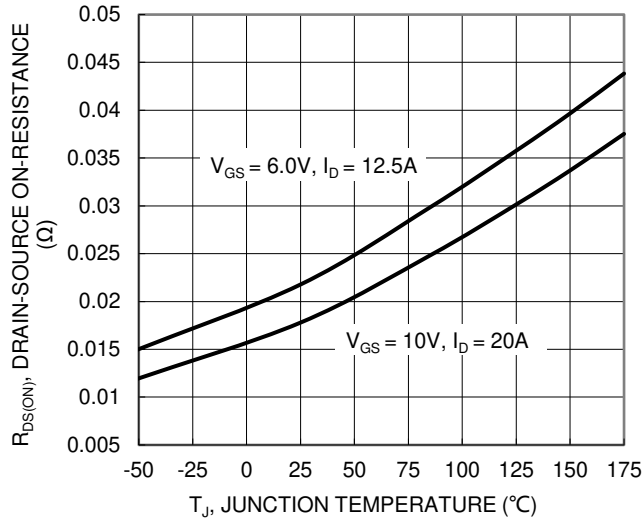


Figure 7. On-Resistance Variation with Temperature

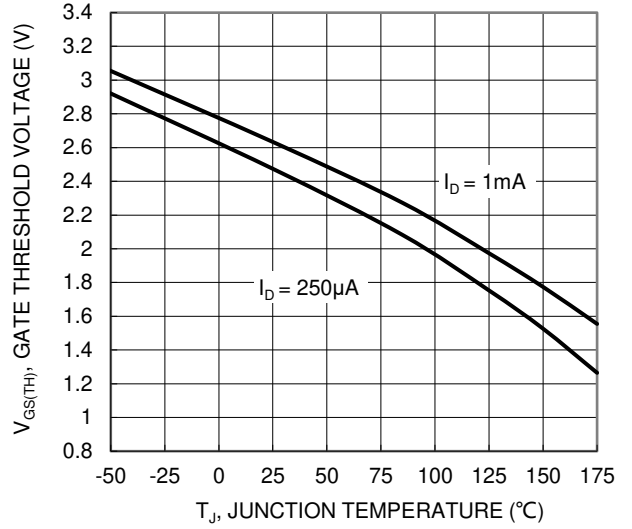


Figure 8. Gate Threshold Variation vs. Junction Temperature

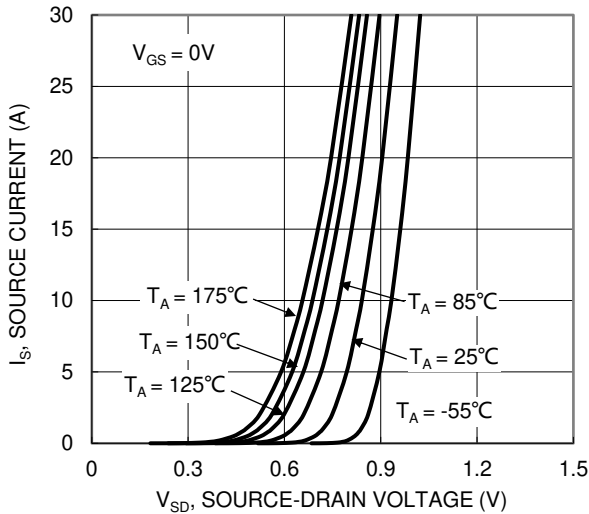


Figure 9. Diode Forward Voltage vs. Current

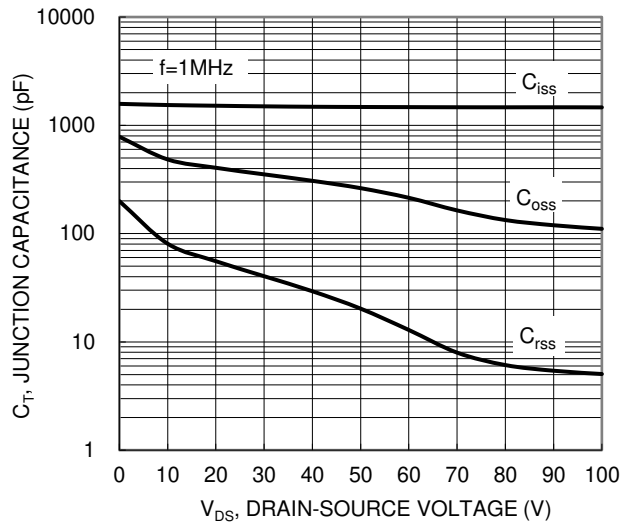


Figure 10. Typical Junction Capacitance

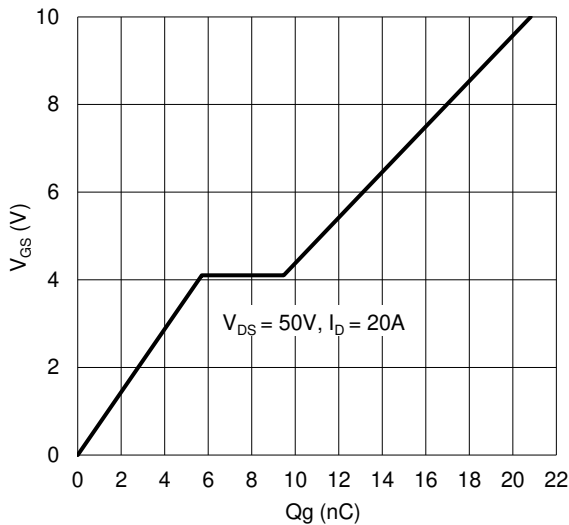


Figure 11. Gate Charge

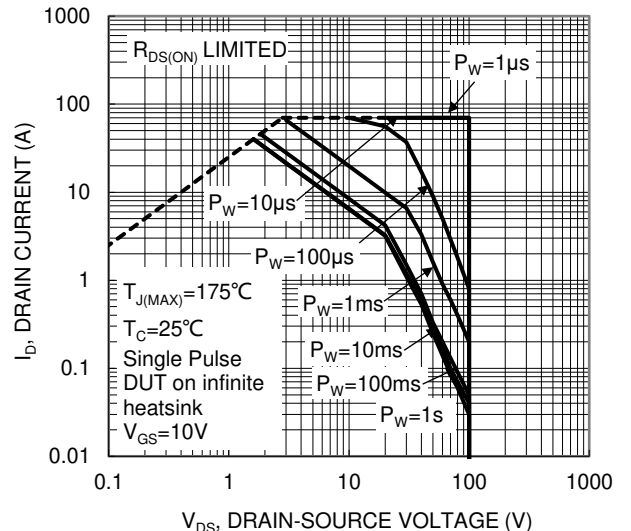


Figure 12. SOA, Safe Operation Area

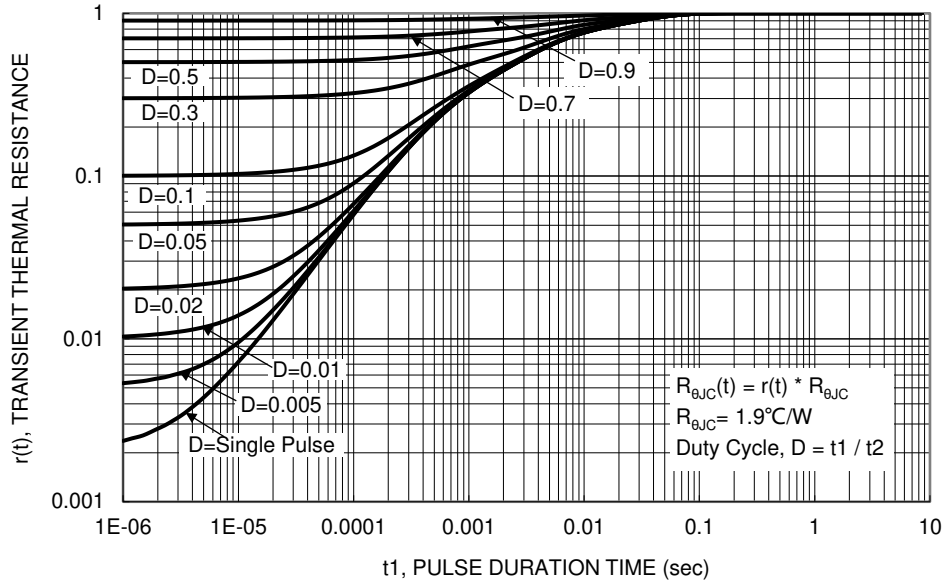


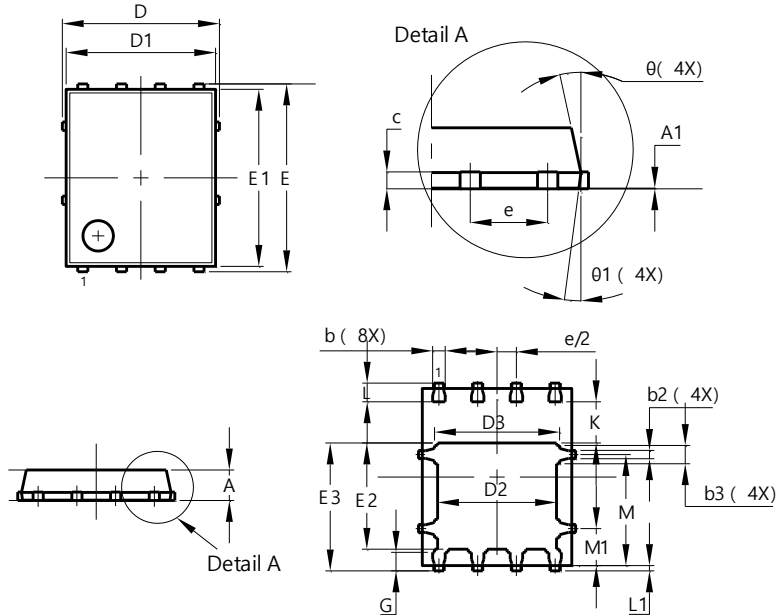
Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

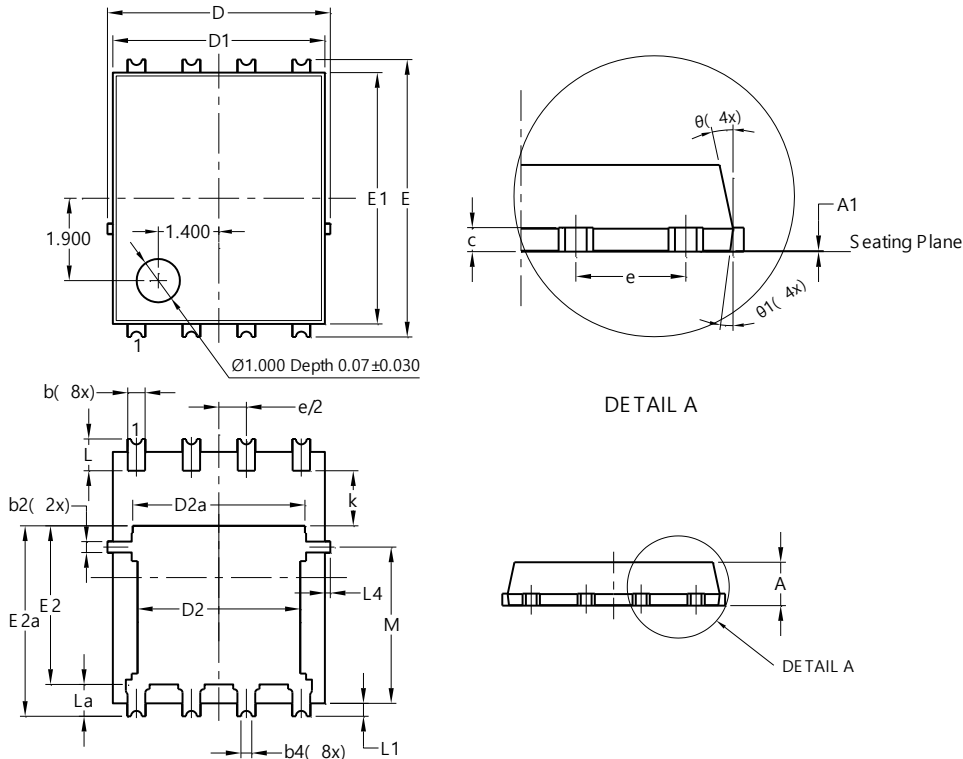
**PowerDI5060-8**



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Site 2:

**PowerDI5060-8/SWP (Type UX)**



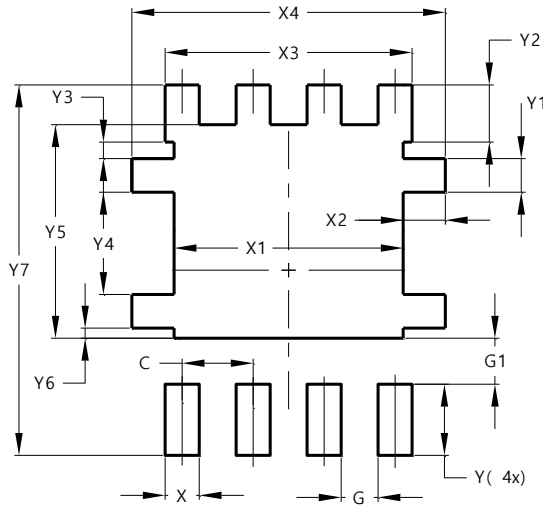
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

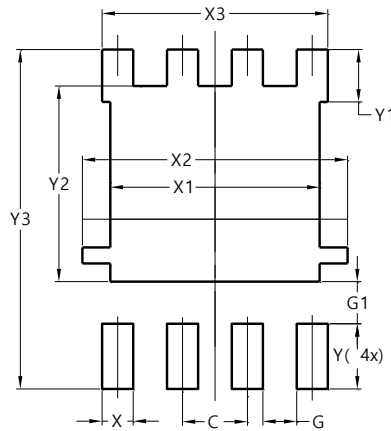
**PowerDI5060-8**



Dimensions	Value (in mm)
<b>C</b>	1.270
<b>G</b>	0.660
<b>G1</b>	0.820
<b>X</b>	0.610
<b>X1</b>	4.100
<b>X2</b>	0.755
<b>X3</b>	4.420
<b>X4</b>	5.610
<b>Y</b>	1.270
<b>Y1</b>	0.600
<b>Y2</b>	1.020
<b>Y3</b>	0.295
<b>Y4</b>	1.825
<b>Y5</b>	3.810
<b>Y6</b>	0.180
<b>Y7</b>	6.610

Site 2:

**PowerDI5060-8/SWP (Type UX)**



Dimensions	Value (in mm)
<b>C</b>	1.270
<b>G</b>	0.660
<b>G1</b>	0.820
<b>X</b>	0.610
<b>X1</b>	4.100
<b>X2</b>	5.190
<b>X3</b>	4.420
<b>Y</b>	1.270
<b>Y1</b>	1.020
<b>Y2</b>	3.810
<b>Y3</b>	6.610



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